High Voltage Power Transistors

DPAK For Surface Mount Applications

Designed for line operated audio output amplifier, switchmode power supply drivers and other switching applications.

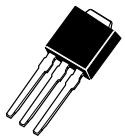
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("–1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular MJE340 and MJE350
- 300 V (Min) — $V_{CEO(sus)}$
- 0.5 A Rated Collector Current

NPN
MJD340*
PNP
MJD350*

*ON Semiconductor Preferred Device

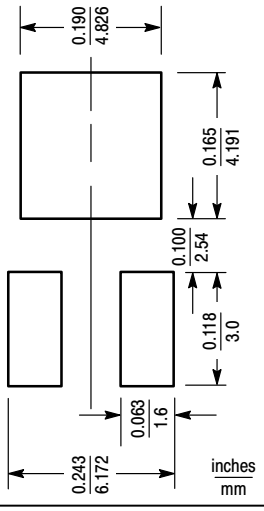
SILICON
POWER TRANSISTORS
0.5 AMPERE
300 VOLTS
15 WATTS

CASE 369A–13



CASE 369–07

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	300	Vdc
Collector–Base Voltage	V_{CB}	300	Vdc
Emitter–Base Voltage	V_{EB}	3	Vdc
Collector Current — Continuous — Peak	I_C	0.5 0.75	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12	Watts W/°C
Total Power Dissipation* @ T_A = 25°C Derate above 25°C	P_D	1.56 0.012	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance, Junction to Ambient*	$R_{\theta JA}$	80	°C/W
Lead Temperature for Soldering Purpose	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I_C = 1 mAdc, I_B = 0)	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current (V_{CB} = 300 Vdc, I_E = 0)	I_{CBO}	—	0.1	mAdc
Emitter Cutoff Current (V_{BE} = 3 Vdc, I_C = 0)	I_{EBO}	—	0.1	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc)	h_{FE}	30	240	—

*When surface mounted on minimum pad sizes recommended.
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

TYPICAL CHARACTERISTICS

MJD340

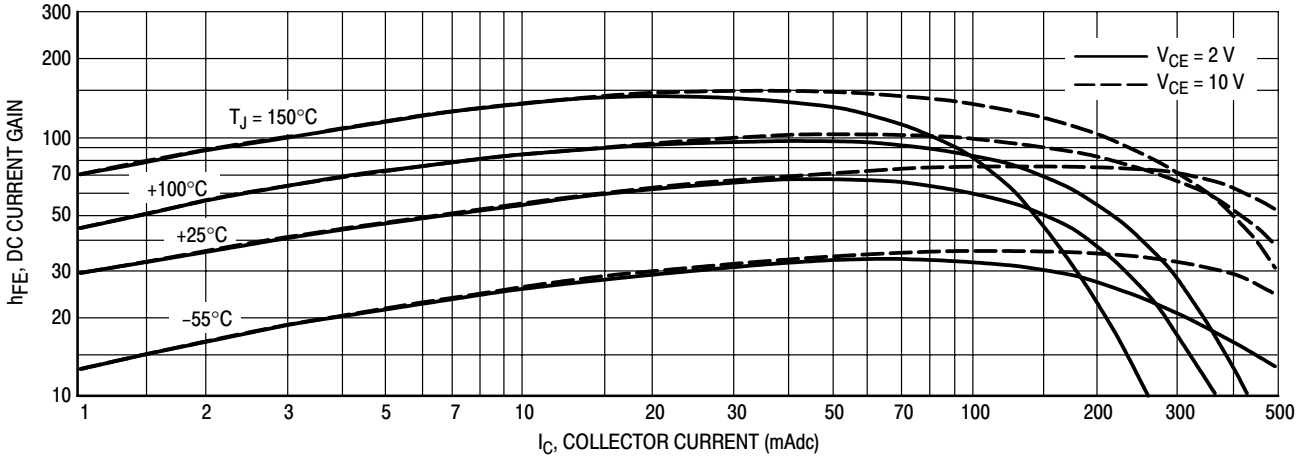


Figure 1. DC Current Gain

MJD340

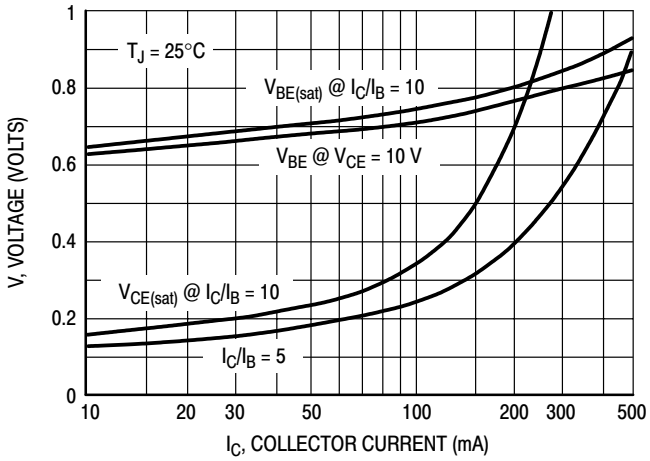


Figure 2. “On” Voltages

MJD350

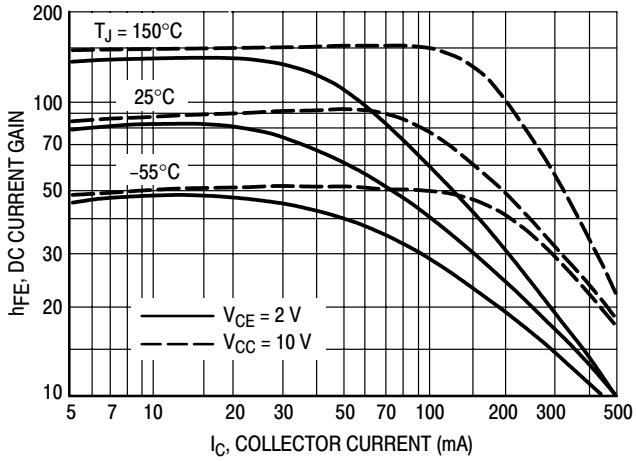


Figure 3. DC Current Gain

MJD350

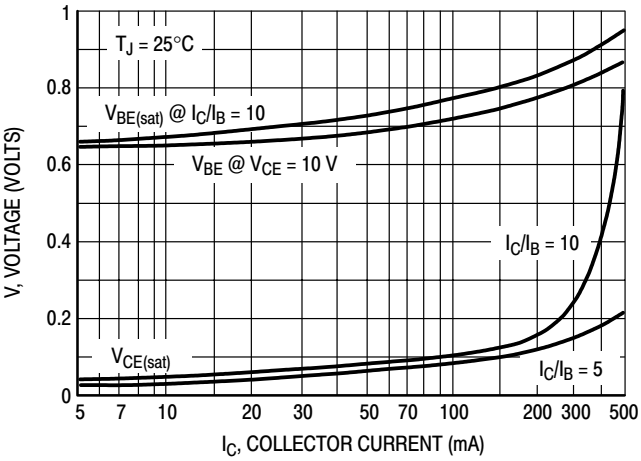


Figure 4. “On” Voltages

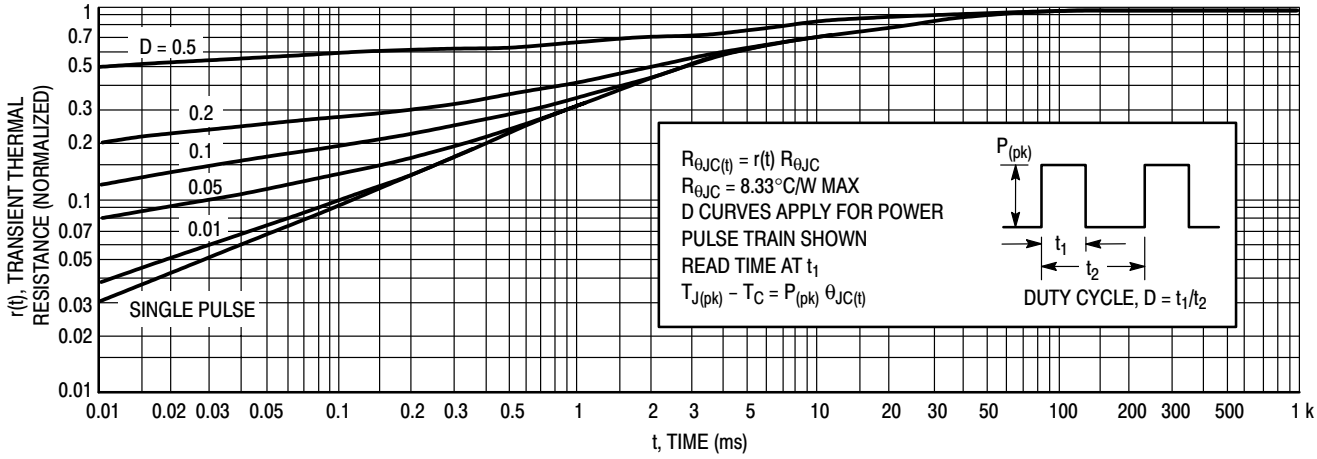


Figure 5. Thermal Response

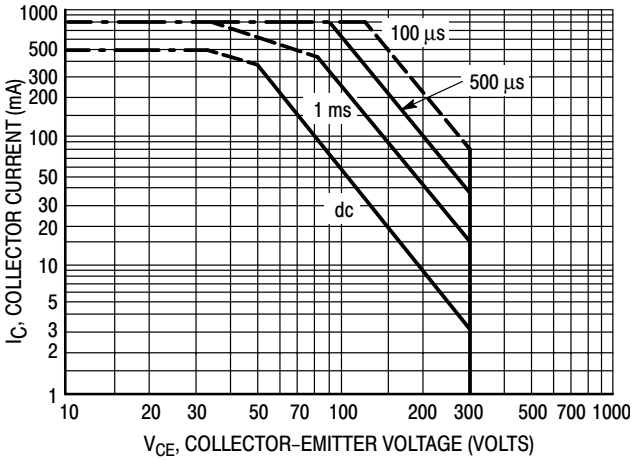


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

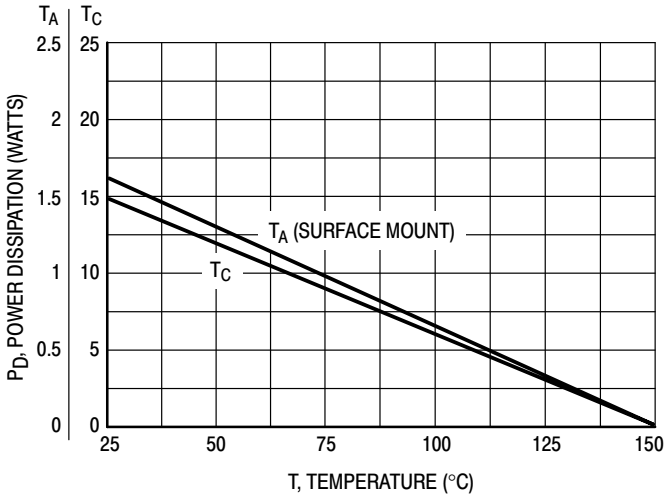
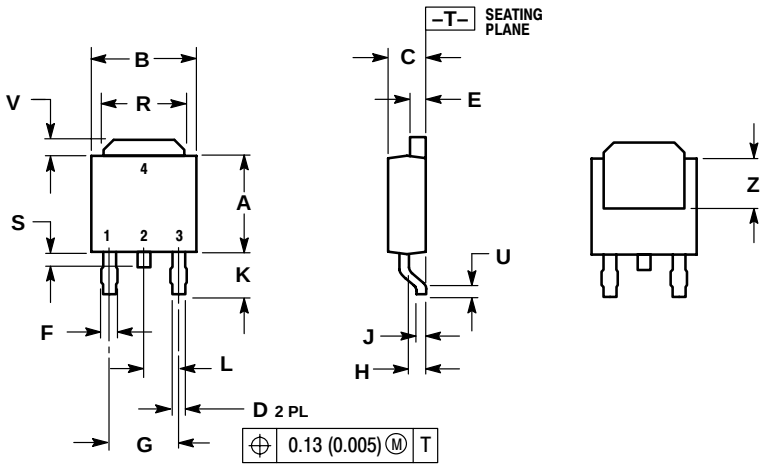


Figure 7. Power Derating

PACKAGE DIMENSIONS

DPAK
CASE 369A−13
ISSUE AA

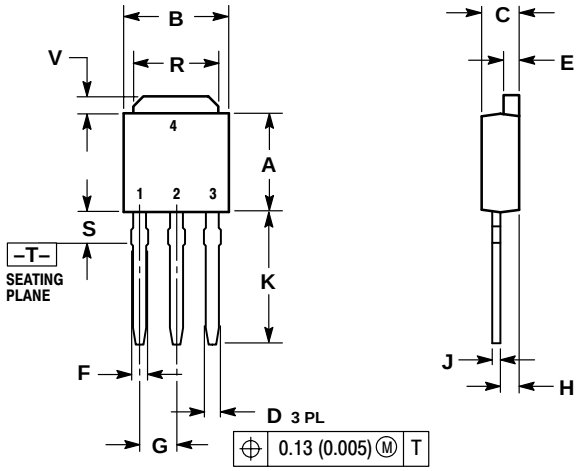


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	---	0.51	---
V	0.030	0.050	0.77	1.27
Z	0.138	---	3.51	---

PACKAGE DIMENSIONS

DPAK
CASE 369–07
ISSUE M



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G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

Notes

PUBLICATION ORDERING INFORMATION

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